

Home Assignment - 1 (24EC1204)

1) using the given parameters for single stage CE amplifier with $R_S = 1k\Omega$, $R_i = 50k\Omega$, $R_a = 2k\Omega$, $R_c = 1k\Omega$, $R_L = 1.2k\Omega$, $h_{FE} = 50$, $h_{ie} = 1.1k\Omega$, $h_{oe} = 25\mu A/V$ & $h_{ce} = 2.5 \times 10^{-4}$. Develop the complete h-parameter small-signal model, perform the necessary circuit analysis, then determine A_i , R_i , A_v , A_{io} , A_{os} , R_o ?

Sol:

Given data;

$$R_S = 1k\Omega, R_i = 50k\Omega, R_a = 2k\Omega, R_c = 1k\Omega$$

$$R_L = 1.2k\Omega \quad h_{FE} = 50 \quad h_{ie} = 1.1k\Omega$$

$$h_{oe} = 25 \times 10^{-6} \quad h_{ce} = 2.5 \times 10^{-4}$$

Step 1: To find Current gain A_I ?

$$A_I = \frac{-h_{FE}}{1 + h_{oe} R_2'} \rightarrow ①$$

$$\text{here } R_2' = (R_c || R_L) = \frac{1 \times 10^3 \times 1.2 \times 10^3}{(1+1.2) \times 10^3} = 0.545k\Omega$$

$$= \frac{-50}{1 + (25 \times 10^{-6})(545)}$$

$$\boxed{A_I = -49.33}$$

Step 2: Input resistance R_i ?

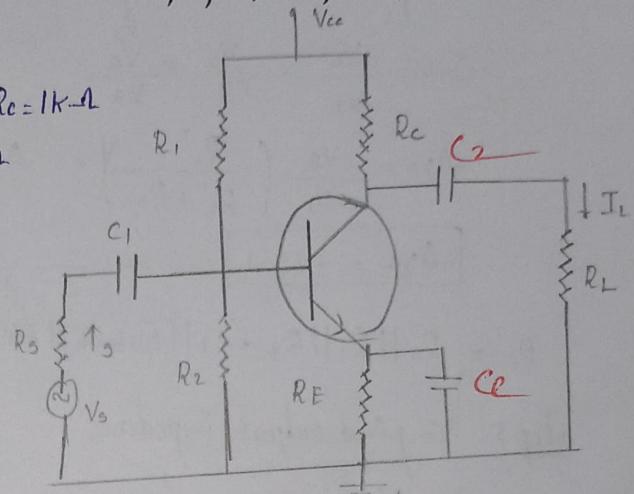
$$\begin{aligned} R_i &= h_{ie} + h_{oe} A_I R_2' \\ &= 1.1 \times 10^3 + 2.5 \times 10^{-4} (-49.33)(0.545) \\ &= 3.6 \times 10^3 (-49.33)(0.545) \end{aligned}$$

$$\boxed{R_i = 1093\Omega}$$

Step 3: Voltage gain A_v ?

$$\begin{aligned} A_v &= \frac{V_2}{V_1} = \frac{A_I R_2'}{R_i} \\ &= \frac{-49.33 \times 0.545}{1093} \end{aligned}$$

$$\boxed{A_v = -84.61}$$

Step 4: To find A_{os}

$$A_{os} = A_i \frac{R_c || R_L}{R_i || R_2 + R_i} \rightarrow ②$$

$$R_i || R_2 = 1.923k\Omega$$

$$= -49.33 \times \frac{1.923 \times 10^3}{1.923 \times 10^3 + 1.093 \times 10^3}$$

$$= -49.33 \times \frac{1.923}{3.013}$$

$$\boxed{A_{os} = -31.49}$$

Step 6: To find Voltage gain A_v ?

$$A_v = \frac{V_c}{V_B} = \frac{A_i R_L'}{R_E} = -\frac{49.32 \times 545.45}{1093} = -24.61$$

Step 7: To find Source Voltage A_{v0}

$$A_{v0} = \frac{V_c}{V_S} = \frac{V_c}{V_B} \times \frac{V_B}{V_S}$$

$$A_{v0} = \frac{V_a}{V_I} \left(\frac{R_L'}{R_L' + R_S} \right) = A_v \left(\frac{R_L'}{R_L' + R_S} \right) = 24.61 \left(\frac{696.9}{10^3 + 696.9} \right)$$

$$\boxed{A_{v0} = -10.1}$$

$$R_L' = R_{L1} \parallel R_{L2} = 1150k\Omega \parallel 2k\Omega = 696\Omega$$

Step 8: To find output impedance

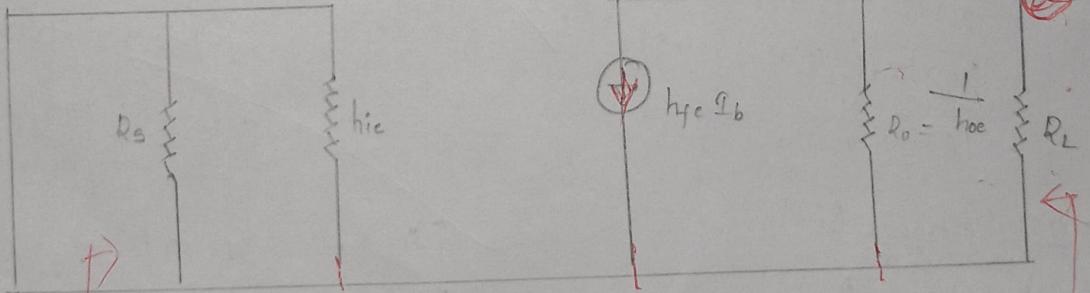
$$R_o' = \frac{V_{out}}{I_{out}} = \frac{1}{h_{oe} + \frac{h_{fe}h_{re}}{R_E + h_{ie}}} = 55.4k\Omega$$

$$R_o = R_{L1} \parallel R_o' = 1k\Omega \parallel 55.4k\Omega = 0.982k\Omega$$

Q) For CE amplifier using an PNP transistor with $h_{ie} = 1200 \text{ ohms}$, $h_{ore} = 0$, $h_{fe} = 36$, $h_{oe} = 2 \times 10^{-6} \text{ mho}$, $R_E = 2.5k\Omega$ & source Resistance $R_S = 500\Omega$. Construct the Complete h-parameter small signal model of the circuit? A_v , A_i , R_i , R_o ?

Ans:

h-parameter:



Given data;

$$h_{ie} = 1200\Omega$$

$$h_{oe} = 2 \times 10^{-6}$$

$$R_L = 2500$$

$$h_{ore} = 0$$

$$R_o = \frac{1}{h_{oe}} = 500,000$$

$$R_o = 500\Omega$$

$$h_{fe} = 36$$

Step 1: To find Voltage gain A_v

$$A_v = \frac{-h_{fe} \cdot R_L'}{h_{ie} + R_s} \quad \therefore R_L' = R_L || R_o = 2488 \Omega$$

$$A_v = \frac{-36 \cdot 2488}{1200 + 500} = -\frac{8956.8}{1700}$$

$$\boxed{A_v = -52.69}$$

Step 2: To find Current gain A_I ?

$$A_I = \frac{i_o}{i_s} = \frac{h_{fe} \cdot R_L'}{R_L' + r_o} \quad \boxed{= h_{fe} = 36} \quad (R_L' \ll r_o)$$

Step 3: To find Input resistance R_i ?

$$\boxed{R_i = h_{ie} = 1200 \Omega}$$

Step 4: Output Resistance R_o

$$R_o = \text{small } R_L = \frac{500000 \cdot 2500}{500000 + 2500} \approx 2488$$

$$\boxed{R_o = 2488 \Omega}$$

Design CE amplifier for given Supply Voltage 10V, $I_C = 1.8 \text{ mA}$, $I_{C\min} = 1.75 \text{ mA}$, $I_{C\max} = 2.25 \text{ mA}$, $h_{fe\min} = 180$, $h_{fe\max} = 460$. Assume the lower Cutoff frequency to be 200 Hz ?

Given data :→

$$V_{cc} = 10 \text{ V}$$

$$I_C = 1.8 \text{ mA}$$

$$I_{C\min} = 1.75 \text{ mA} \quad I_{C\max} = 2.25 \text{ mA}$$

~~$$h_{fe\min} \beta_{\max} = 460 \quad h_{fe\max} \beta = 180$$~~

~~$$\text{Low Cut-off frequency } (f_L) = 200 \text{ Hz}$$~~

Choosing CE amplifier Configuration

- i, R_1, R_2 : Voltage divider bias
- ii, R_o - collector resistor
- iii, R_E - Emitter resistor
- iv, C_E - Capacitor across

c_{c1}, c_{c2} - coupling capacitor

R_L - load resistance .

Step 1: To find V_{CE} :

$$V_{CE} = \frac{V_{CC}}{2} = \frac{10}{2} = 5V$$

$$\boxed{V_{CE} = 5V}$$

Source Voltage across R_C is :

$$V_{RC} = V_{CC} - V_{CE} = 10 - 5 = 5$$

$$\boxed{V_{RC} = 5V}$$

Step 2: Find R_E

$$R_E = \frac{V_{RE}}{I_c} = \frac{5}{1.8 \times 10^{-3}} = 2.7k\Omega$$

$$\boxed{R_E = 2.7k\Omega}$$

Step 3: choose R_L for stability

$$V_{RE} \approx 1V$$

$$R_E = \frac{V_{RE}}{I_c} = \frac{1}{1.8 \times 10^{-3}} = 560\Omega$$

3, (Voltage Divider) :

$$V_B = V_E + V_{BE} = 1V + 0.7 = 1.7V$$

$$I_B = \frac{I_c}{\beta} = \frac{1.8 \times 10^{-3}}{180} = 10\mu A$$

$$I_{R_2} = 10 \times I_B = 100\mu A$$

$$\boxed{I_{R_2} = 100\mu A}$$

$$R_2 = \frac{V_B}{I_{R_2}} = \frac{1.7V}{100\mu A} = 17k\Omega$$

$$R_2 = 17k\Omega \rightarrow \textcircled{1}$$

$$R_1 = \frac{V_{CC} - V_B}{I_{R_1}} = \frac{10 - 1.7}{100\mu A} = 83k\Omega$$

$$C = \frac{1}{2\pi f X_C} = \frac{1}{2\pi(200)(1000)}$$

$$\boxed{C = 0.8\mu F}$$

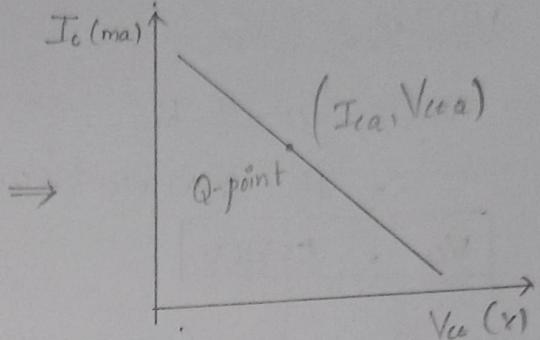
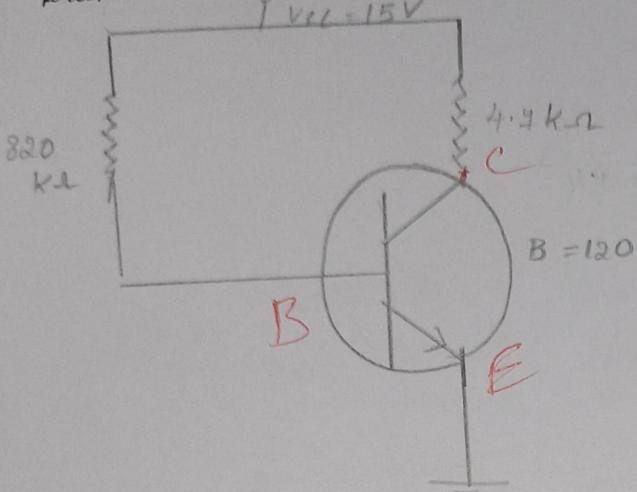
Where $c_{c1} = c_{c2} = 1\mu F$

$$A_v = \frac{-R_C}{R_E} \quad r_{ce} \approx \frac{25mV}{I_c} = \frac{25}{1.8} \approx 13.9\Omega$$



4) sketch dc load line and locate the operating point for fixed biasing.

Transistor Circuit? $V_{BE} = 0.7$



Given Data :

$$V_{CC} = 15V \quad R_B = 820 \times 10^3 \Omega$$

$$R_C = 4.7 \times 10^3 \Omega \quad \beta = 120$$

To find Quiescent operating point (I_{CQ} , V_{CEQ})

Step 1: To find I_B

1, apply kvl @ input loop

$$V_{CC} - I_B R_B - V_{BE} = 0$$

$$I_B R_B = V_{CC} - V_{BE}$$

$$I_B = \frac{V_{CC} - V_{BE}}{R_B} = \frac{15 - 0.7}{820 \times 10^3}$$

$$\boxed{I_B = 1.74 \mu A}$$

Step 2: To find collector current I_C

$$I_C = \beta I_B$$

$$= 120 \times 1.74 \times 10^{-6}$$

$$\boxed{I_C = 2.09 \text{ mA}}$$

steps: To find Voltage at Emitter-Collector

$$V_{ce} - I_c R_c - V_{ce} = 0$$

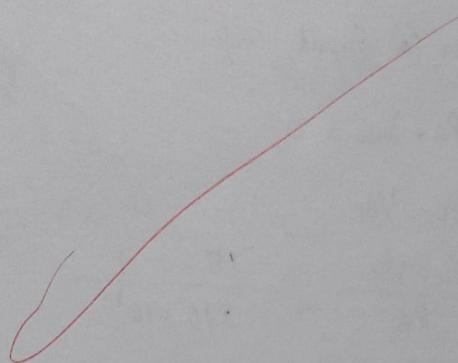
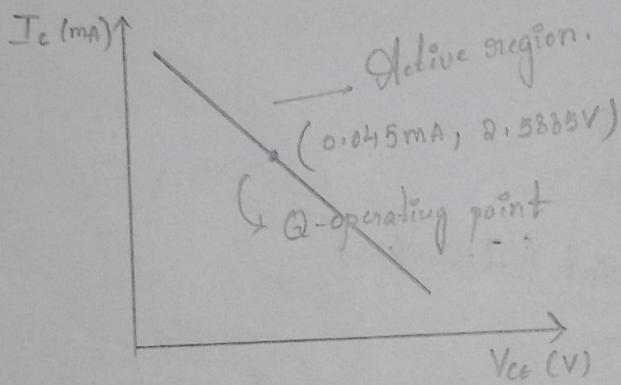
$$V_{ce} = V_{cc} - I_c R_c$$

$$= 15 - 2.09 \times 10^{-3} \times 4.7 \times 10^3$$

$$\boxed{V_{ce} = 5.17 \text{ V}}$$

Quiescent operating point $(\frac{I_{cQ}}{2}, \frac{V_{ceQ}}{2})$

sketching the De load line:

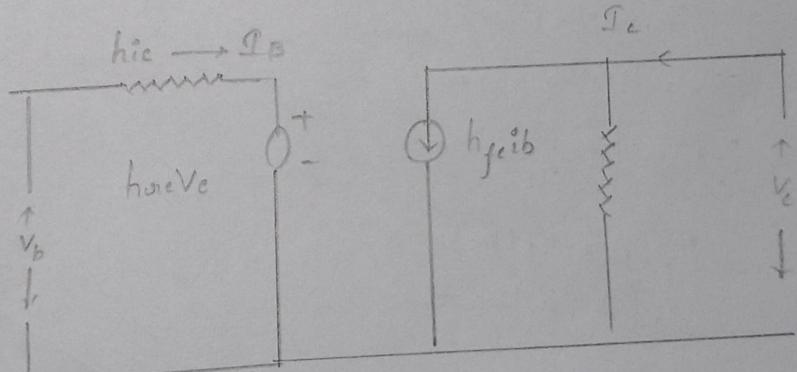
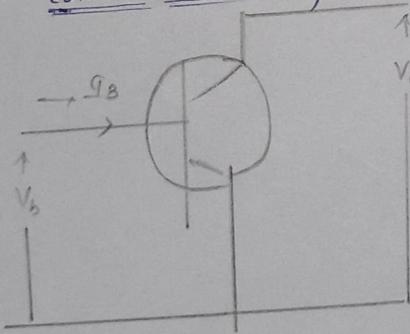


Compare the Characteristic CE, CB, CC transistor con with respect to input resistance output resistance , Current gain!

parameters	Common Emitter	Common Base	Common collector.
Input resistance	Medium ($1k\Omega$)	Very low (tens of Ω)	High (tens of $k\Omega$)
Output resistance	Medium to high ($10k\Omega - 50k\Omega$)	Very high ($100k\Omega$ or more)	Very low (tens to hundred)
Current gain	$\beta = h_{fe}$ typically ($20 - 500$)	Less than 1 ($0.95 - 0.99$)	Very high ($\beta + 1$)
Voltage gain	High (≈ 100)	High ($\approx 50 - 500$)	no amplification.

b) Draw the A-parameter model of CE amplifier model of with Voltage divider bias and Explain the parameter?

Common emitter amplification:



Current gain A_i

$$A_i = \frac{I_2}{I_1} = -\frac{I_2}{I_1}$$

$$I_2 = h_f I_1 + h_o V_2, V_2 = I_1 Z_2 = -I_2 Z_2$$

$$I_2 = h_f I_1 - I_1 Z_2 h_o$$

$$I_2 + I_1 Z_2 h_o = h_f I_1$$

$$I_2 (1 + Z_2 h_o) = h_f I_1$$

$$\boxed{A_i = -\frac{h_f}{1 + Z_2 h_o}}$$

a) Input impedance (Z_i)

$$Z_i = \frac{V_i}{I_i} \rightarrow (1)$$

$$V_i = h_i I_1 + h_{o1} V_2$$

$$Z_i = \frac{h_i I_1 + h_{o1} V_2}{I_1} = h_i + h_{o1} \frac{V_2}{I_1}$$

$$V_2 = -A_T Z_L = A_T Z_1 Z_2$$

$$Z_i = h_i + h_{o1} \frac{A_T Z_1 Z_2}{Z_1}$$

$$Z_i = h_i + h_{o1} A_T Z_2$$

$$Z_i = h_i + h_{o1} \frac{h_f}{1 + h_{o1} Z_2}$$

$$\boxed{Z_i = h_i + h_{o1} \frac{h_f}{Y_L + h_o}}$$

b) Output admittance:

$$Y_o = I_2 / V_2$$

$$I_2 = h_{fe} I_1 + h_o V_2$$

$$\frac{I_2}{V_2} = h_f \frac{I_1}{Z_2} + h_o$$

$$R_s I_1 + h_i I_1 + h_{o1} V_2 = 0$$

$$I_1 (R_s + h_i) + h_{o1} V_2 = 0$$

$$\frac{I_1}{V_2} = \frac{-h_{o1}}{R_s + h_i}$$

$$\boxed{Y_o = \frac{h_o + h_f h_{o1}}{R_s + h_i}}$$

c) Voltage gain (A_v)

$$A_v = V_2 / V_1$$

$$V_2 = -A_T Z_1 = A_T Z_1 Z_2$$

$$A_v = \frac{A_T Z_1 Z_2}{V_1} = \frac{A_T Z_2}{V_1 / Z_1}$$

$$\boxed{A_v = \frac{A_T Z_2}{Z_i}}$$

b) Voltage gain

$$A_v = \frac{A_T R_L}{Z_i}$$

~~QD~~

Home Assignment - 8 (84 EC 2104)

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1. For the FET biasing Circuit shown in figure, utilize the necessary equation using the device's characteristic relation and perform a Complete DC bias analysis. To determine?

$$1) V_{DSQ} \quad 2) I_{DQ} \quad 3) V_{DSQ} \quad 4) V_D$$

Sol:

Given Data from the Circuit

$$R_G = 1M\Omega \quad V_{G1G1} = 2V$$

$$R_D = 1k\Omega \quad V_{cc} = 8V$$

1) Apply kvl at Input loop:

$$-V_{G1S} - V_{G1G1} - I_{G1}R_G = 0 \quad \therefore (I_{G1} = 0)$$

$$-V_{G1S} - V_{G1G1} = 0$$

$$-V_{G1S} = V_{G1G1}$$

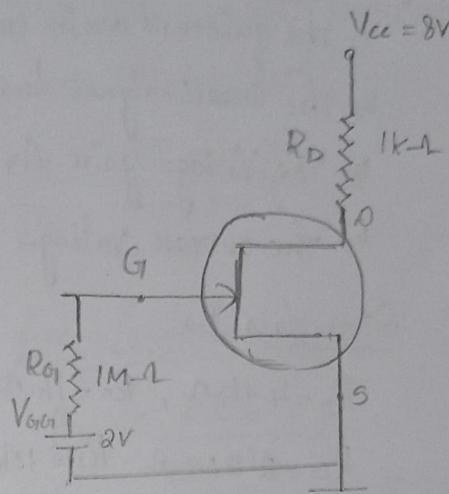
$$\boxed{V_{G1S} = -V_{G1G1} = -2V}$$

2) To find I_{DQ} :

Apply shokley's equation

$$\begin{aligned} I_D &= I_{DSQ} \left(1 - \frac{V_{GS}}{V_p} \right)^n \\ &= 10 \times 10^{-3} \left(1 - \frac{(-2)}{(-4)} \right)^n \\ &= 10 \times 10^{-3} \left(1 - \frac{1}{2} \right)^n \\ &= 10 \times 10^{-3} \left(\frac{1}{2} \right)^2 \\ &= 10 \times 10^{-3} \left(\frac{1}{4} \right) \end{aligned}$$

$$\boxed{I_D = 2.5mA}$$



$$\begin{aligned} 3) V_{DS} &= V_{cc} - I_D R_D \\ &= 8 - 2.5 \times 10^3 \quad (1 \times 10^3) \\ &= 8 - 2.5 \\ \boxed{V_{DS} &= 5.5V} \end{aligned}$$

(D)
(D)
(S)

$$\begin{aligned} 4) V_D &= V_D - V_S \\ V_D &= V_{DS} + V_S \quad . (V_S = 0) \end{aligned}$$

$$V_D = V_{DS} = 5.5V$$

$$\boxed{V_D = 5.5V}$$

- a) A common source MOSFET amplifier has $R_D = 4.7k\Omega$, $R_S = 1k\Omega$ (bypassed), $R_G = 2.8M\Omega$, $R_L = 10k\Omega$, $V_{DD} = 15V$, $k_n = 2.5mA/V^2$, $V_{th} = 2V$. If the signal amplitude is 25 mV, peak calculate.

- 1, The quiescent drain current I_D , drain to source V_{DS}
- 2, The small-signal transconductance g_m
- 3, The voltage gain A_v ignoring R_L
- 4, The overall voltage considering R_L

Given:

Given data :→

$$R_D = 4.7k\Omega, R_S = 1k\Omega \text{ (bypass for AC)}$$

$$R_G = 2.8M\Omega, R_L = 10k\Omega, V_{DD} = 15V, k_n = 2.5 \times 10^{-3} A/\mu$$

$$V_{th} = 2V, V_{in} = 25mV, V_{peak} = 0.025V$$

- 1, The quiescent I_D and V_{DS} :→

since Gate Current is negligible ($I_G = 0$)

$$V_G = 0 \rightarrow ①$$

calculate V_S :→

$$V_S = I_D R_S \text{ or } I_S R_S$$

calculate V_{GS} :→

$$V_{GS} = V_G - V_S \\ = 0 - I_D R_S$$

$$V_{GS} = -I_D R_S \rightarrow ②$$

Drain Current

$$I_D = k_n (V_{GS} - V_{th})^y$$

$$I_D = k_n (-I_D R_S - V_{th})^y$$

$$I_D = k_n (V_{GS} - V_{th})^y$$

$$I_D = k_n (-I_D R_S - V_{th})^y$$

$$= k_n (-I_D R_S - V_{th})^y$$

$$= k_n (V_{th} + I_D R_S)^y$$

$$I_D = 2.5y^y - y + 2 = 0$$

$$\text{where } V_G = 0$$

assume $V_{G_1} = 5V \rightarrow$

$$V_{G_{1S}} = V_{G_1} - I_D R_S = 5 - 1000 I_D$$

$$I_D = k_n (V_{G_{1S}} - V_{th})^n$$
$$= 2.5 \times 10^{-3} (5 - 1000 I_D - 2)^n$$

$$= 2.5 \times 10^{-3} (3 - 1000 I_D)^n$$

let $x = I_D \rightarrow \textcircled{1}$

$$x = 2.5 \times 10^{-3} (3 - 1000 x)^n$$

Set $y = 3 - 1000 x$

$$x = 0.025y^n$$

$$y = 3 - 1000x = 3 - 1000 (0.025y^n)$$

$$= 3 - 2.5y^n$$

$$y + 2.5y^n = 3$$

$$2.5y^n + y - 3 = 0$$

Solve quadratic equation

$$y_1 = 0.914$$

$$y_2 = -1.314$$

Find I_D :

$$I_D = 0.025y^n$$
$$= 0.025 (0.914)^n$$

$$\boxed{I_D = 2.09mA}$$

Calculate V_{DS} :

$$V_{DS} = V_{DD} - I_D (R_D + R_S)$$

$$= 15 - 2.09 \times 10^{-3} (4700 + 1000)$$

$$= 15 - 2.09 \times 10^{-3} (5700)$$

$$= 15 - 11.913$$

$$\boxed{V_{DS} = 3.087V}$$

Trans Conductance:

$$g_m = \frac{2I_D}{V_{GS} - V_{th}}$$
$$= \frac{2(2.09mA)}{2.91 - 2}$$

$$\boxed{g_m = 4.6ms}$$

Voltage gain A_v ignoring R_2

$$A_v = -g_m R_D$$

$$= -4.6 \times 4700 \times 10^{-3}$$

$$= -21.62$$

Overall Voltage gain

$$A_v = -g_m R_{load}$$

$$= -0.0046 \times 3197$$

$$\boxed{= -14.7}$$

3) For the given Circuit shown in the figure, Estimate the input impedance, output impedance and Voltage gain?

Sol:

Given Data :

$$R_D = 5.1 \text{ k}\Omega, g_m = 2 \text{ mS} < 0.0025$$

$$\pi_{lo} = 50 \text{ k}\Omega, R_{G1} = 1 \text{ M}\Omega$$

1) Input impedance (Z_{in}):

JFET gate Voltage Source $V_{G1} = 0$

$$\text{where } Z_{in} = R_{G1} = 1 \text{ M}\Omega$$

2) Output impedance (Z_{out}):

$$Z_{out} \approx (R_D \parallel \pi_{lo})$$

$$= \frac{R_{D\text{pro}}}{R_D + \pi_{lo}} = \frac{5100 \times 50000}{5100 + 50,000} = \frac{255,000,000}{55,000}$$

$$\boxed{Z_{out} = 4627 = 4.63 \text{ k}\Omega}$$

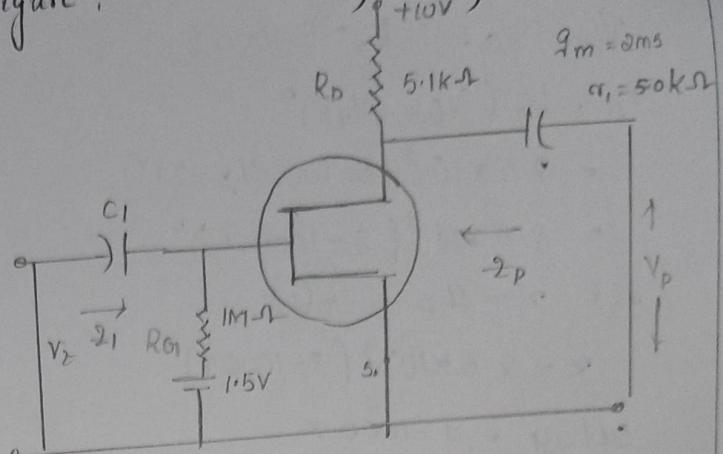
3) Voltage gain:

$$A_V = \frac{V_o}{V_i} \quad \text{where } A_V = -g_m (R_D \parallel \pi_{lo})$$

$$A_V = -g_m (4627) = -0.002 \times 4627 = -9.25$$

$$\boxed{A_V = -9.25 \text{ V}}$$

4) ~~For mosfet amplifier with $V_{DD} = 15 \text{ V}$, $R_D = 3.3 \text{ k}\Omega$, $R_S = 1 \text{ k}\Omega$ (by passed), $R_{G1} = 2 \text{ M}\Omega$, $R_2 = 5 \text{ k}\Omega$, $k_n = 2 \text{ mA/V}^2$ and $V_{th} = 1.5 \text{ V}$ Estimate the quiescent operating point and Evaluate the overall Voltage~~



Given Data :→

$$V_{DD} = 15V, R_D = 3.3k\Omega, R_S = 1k\Omega \text{ (bypassed)}$$

$$R_G = 1M\Omega, R_2 = 5k\Omega, k_n = 2 \times 10^3 A/V^2, V_{th} = 1.5V$$

To find Quiescent operating point (I_{DQ}, V_{DSQ}) :→

$$\text{where } I_D = k_n (V_{GS} - V_{th})^2 \rightarrow (1)$$

$$V_{GS} = V_g - V_b \rightarrow V_{GS} = -V_b \quad \therefore (V_b = I_D R_S)$$

$$V_{GS} = -I_D R_S = -I_D R_S \quad \therefore (I_D = I_S)$$

$$V_{GS} = -I_D R_S \rightarrow \text{sub ineq-1}$$

$$I_D = k_n (-I_D R_S - V_{th})^2 \quad (R_S = 1 \times 10^3) \quad (V_{th} = 1.5)$$

$$I_D = k_n (-I_D 10^3 - V_{th})^2 = k_n (-I_D 10^3 - 1.5)^2$$

let us assume $I_D = x \text{ mA}$

$$I_D = 0.002 (10^3 x + 1.5)^2 = 0.002 (10^6 x^2 + 3000x + 2.25)$$

$$x = 2000x^2 + 6x + 0.0045$$

$$I_D = 2000I_P^2 + 6I_P + 0.0045 \Rightarrow 2000I_P^2 + 5I_P + 0.0045 = 0$$

Discriminant $b^2 - 4ac = -11 < 0$

$$\therefore V_{GS} = 0 \quad I_D = k_n (-V_{th})^2$$

$$I_D = (-10^3 I_D + 1.5)^2 = \frac{-4 \pm \sqrt{49 - 36}}{4000} = \frac{-4 \pm \sqrt{13}}{4000}$$

$$\boxed{I_{D1} = 0.848 \text{ mA}}, \boxed{I_{D2} = 2.65 \text{ mA}}$$

$$V_D = V_{DD} - I_D R_D = 15 - (0.00265)(3300) = 6.25$$

$$V_{DS} = V_D - V_b = 6.25 - 2.65 \boxed{= 3.6V}$$

$$V_b = I_D R_S = 2.65 \times 10^{-3} \times 1000 \boxed{= 2.65V}$$

Overall Voltage gain :

$$A_v = -g_m (R_D || r_2) \rightarrow ②$$

$$A_v = -g_m (1988) \rightarrow ③$$

$$R_D || r_2 = \frac{R_D R_T}{R_D + r_2} = \frac{3300 \times 5000}{3300 + 5000} = \frac{16.5 \times 10^6}{8300}$$

To find g_m transconductance

$$g_m = 2kn(V_{gs} - V_t) \quad V_{th} = -1.5$$

$$= 2(0.02)(-2.65 - (-1.5))$$

$$= 2(0.02)(-1.5) \quad \text{than magnitude}$$

$$= 2(0.02)(1.5)$$

$$= 4.6 \rightarrow \text{keep in } ③$$

$$A_v = -4.6(1988) = -9.15$$

$$\boxed{A_v = -9.15}$$

- 5) A self biased n-channel JFET has $V_{DD} = 18V$, $R_D = 2.2k\Omega$, $R_S = 1.5k\Omega$, $I_{DSS} = 10mA$ and $V_P = -4V$ using relevant equation determine I_D , V_{GS} , V_{DS} ?

Sol: Given data :

$$V_{DD} = 18V \quad R_D = 2.2 \times 10^3 \quad R_S = 1.5 \times 10^3 \quad I_{DSS} = 10 \times 10^{-3} \quad V_P = -4V$$

To find I_D :

Apply Shockley's equation $I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P} \right)^2 \rightarrow ②$

Where $V_{GS} = V_g - V_s \quad \because (V_g = 0) \text{ grounded}$

$$V_g = -V_s = -I_s R_S = -I_D R_S \quad \because (I_D = I_s) \rightarrow \text{keep in } ②$$

$$I_D = I_{DSS} \left(1 - \frac{\left(\frac{I_D R_S}{-4} \right)}{\left(\frac{I_D R_S}{-4} \right)} \right)^2 = I_{DSS} \left(1 - \frac{I_D R_S}{4} \right)^2$$

$$= I_{DSS} \left(1 - \frac{I_D (1.5 \times 10^3)}{4} \right)^2$$

$$\begin{aligned}
 I_D &= P_{D00} (1 - 375 I_D)^2 \\
 &= 0.01 (1 - 750 I_D + 140625 I_D^2) \\
 \Rightarrow 1406.25 I_D^2 - 8.5 I_D + 0.01 &= 0
 \end{aligned}$$

Solving Quadratic equation.

$$\boxed{I_{D1} = 4.4 \times 10^{-3}} \quad \boxed{I_{D2} = 1.6 \times 10^{-3}}$$

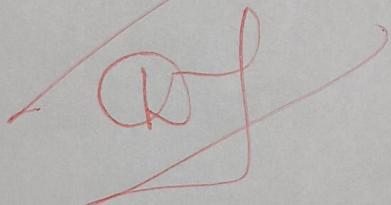
$$\text{where } V_S = P_D R_S = 1.6 \times 10^{-3} \times 1.5 \times 10^3 = 2.400 \text{ V}$$

$$V_{G10} = V_S = -2.400 \text{ V}$$

$$V_D = V_{DD} - P_D R_S = 13 - (1.6 \times 10^{-3})(2200) = 14.48$$

$$\begin{aligned}
 V_{DS} &= V_D - V_S \\
 &= 14.48 - 2.40 = 12.08 \text{ V}
 \end{aligned}$$

$$\boxed{V_{DS} = 12.08 \text{ V}}$$



 QJ